HIGH-CURRENT DARLINGTON TRANSISTOR ARRAYS

DESCRIPTION

The ULN2803 is high-voltage high-current Darlington transistor arrays each containing eight open collector common emitter pairs. Each pair is rated at 500mA. Suppression diodes are included for inductive load driving, the inputs and outputs are pinned in opposition to simplify board layout.

The ULN2803 is capable of driving a wide range of loads including solenoids, relays, DC motors, LED displays, filament lamps, thermal print-heads and high-power buffers.

The ULN2803 is available in SOP18 package.

FEATURES

- 500mA-Rated Collector Current (Single Output)
- High-Voltage Outputs: 50V
- **Output Clamp Diodes**
- Inputs Compatible with Various Types of Logic
- Relay-Driver Applications

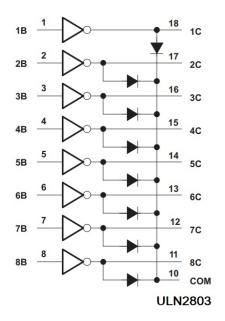
APPLICATION

- Relay Drivers
- **Hammer Drivers**
- Lamp Drivers
- Display Drivers (LED and Gas Discharge)
- Line Drivers
- Logic Buffers

ORDERING INFORMATION

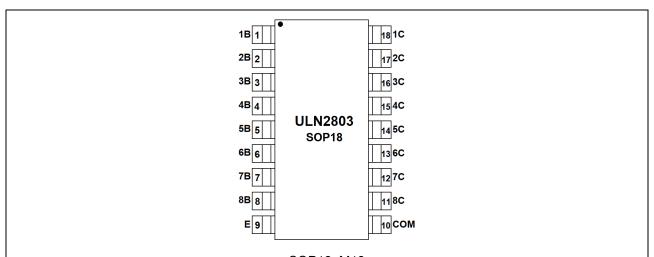
Package Type	Part Number		
SOP18	ULN2803M18R		
SPQ: 2,000/Reel	ULN2803M18VR		
Nata	V: Halogen Free Package		
Note	R: Tape & Reel		
AiT provides all RoHS Compliant Products			

FUNCTIONAL DIAGRAM



SOP18

PIN DESCRIPTION



SOP18, M18 Top View

Pin #	Symbol	Functions	
SOP18			
1	1B	Input pair1	
2	2B	Input pair2	
3	3B	Input pair3	
4	4B	Input pair4	
5	5B	Input pair5	
6	6B	Input pair6	
7	7B	Input pair7	
8	8B	Input pair8	
9	Е	Common Emitter (Ground)	
10	COM	Common Clamp Diodes	
11	8C	Output pair8	
12	7C	Output pair7	
13	6C	Output pair6	
14	5C	Output pair5	
15	4C	Output pair4	
16	3C	Output pair3	
17	2C	Output pair2	
18	1C	Output pair1	

DARLINGTON TRANSISTOR HIGH-CURRENT DARLINGTON TRANSISTOR ARRAYS

ABSOLUTE MAXIMUM RATINGS

At 25°C free-air temperature (unless otherwise noted)

At 25 C free-all temperature (unless otherwise floted)				
V _{CC} , Collector to Emitter Voltage		50\		
V _R , Clamp Diode Reverse Voltage (1)		50V		
V _I , Input Voltage (1)		30V		
Icp, Peak Collector Current	See Typical Characteristics	500mA		
Iok, Output Clamp Current		500mA		
ITE, Total Emitter-Terminal Current		-2.5A		
T _A , Operating Free-Air Temperature Range		-30°C ∼ + 105°C		
θ _{JA} , Thermal Resistance Junction-to-Ambient ⁽²⁾		63°C/W		
θ _{JC} , Thermal Resistance Junction-to-Case ⁽³⁾		12°C/W		
T _J , Operating Virtual Junction Temperature		150°C		
T _{STG} , Storage Temperature Range		-40°C ∼ + 150°C		

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

- (1) All voltage values are with respect to the emitter/substrate terminal E, unless otherwise noted.
- (2) Maximum power dissipation is a function of $T_{J \text{ (max)}}$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is PD = $(T_{J \text{ (max)}} T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
- (3) Maximum power dissipation is a function of $T_{J \text{ (max)}}$, θ_{JC} , and T_{A} . The maximum allowable power dissipation at any allowable ambient temperature is PD = $(T_{J \text{ (max)}} T_{A})/\theta_{JC}$. Operating at the absolute maximum T_{J} of 150°C can affect reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Max.	Units
Vcc	Collector to Emitter voltage		50	V



ELECTRICAL CHARACTERISTICS

 $T_A = 25$ °C, unless otherwise specified

$T_A = 25^{\circ}C$, unless otherw	ise specified								
Parameter	Symbol	Test Figure	Conditions		Min.	Тур.	Max.	Unit	
On Chata lanut				I _C = 200mA	-	ı	2.4		
On-State Input	V _{I (on)}	Fig6	V _{CE} = 2V	I _C = 250mA	-	ı	2.7	V	
Voltage				I _C = 300mA	-	ı	3.0		
Collector-Emitter			I _I = 250μA	I _C = 100mA	-	0.9	1.1		
Saturation Voltage	V _{CE} (sat)	Fig 5	I _I = 350μA	I _C = 200mA	-	1.0	1.3	V	
Saturation voitage			I _I = 500μA	I _C = 350mA	-	1.2	1.6		
Collector Cutoff		Fig1	V _{CE} = 50V	I ₁ =0	-	-	50		
Current	I _{CEX}	Fig2	V _{CE} = 50V	I ₁ =0			100	μΑ	
Current		Fig2	T _A =+105°C	11 -0	-	-	100		
Clamp Forward Voltage	VF	Fig 8	I _F = 350mA		-	1.7	2	V	
Off-State Input	I _{I(OFF)}	Fig3	V _{CE} = 50V, I _C = 500μA		50	65	_	μA	
Current	1(011)	90	VGL 001,10		00			μΛ	
Input Current	l _l	Fig4	V _I = 3.85V		-	0.93	1.35	mA	
Clamp Reverse	I _R	Fig7 V _P = 50V	Fig7 V _R = 50V -	\/ 50\/	-	-	-	50	μA
Current	IK.	1 197	VR - 30 V	T _A = 70°C	-	-	100	μπ	
Input Capacitance	Ci	-	V _I = 0, f = 1MHz		-	15	25	pF	
SWITCHING CHARACT	TERISTICS .	T	T		1				
Propagation Delay									
Time, Low- to	t PLH	Fig9	-		-	0.25	1.00	μs	
High-Level Output									
Propagation Delay									
Time, High- to	t PHL	Fig9	-		-	0.25	1.00	μs	
Low-Level Output									
High-Level Output									
Voltage After	V _{OH}	Fig9	$V_S = 50V, I_O$	= 300mA	VS-20	-	-	mV	
Switching									



TYPICAL PERFORMANCE CHARACTERISTICS

www.ait-ic.com

Fig 1. ICEX Test Circuit

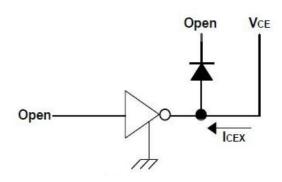


Fig 3. I_{I(OFF)} Test Circuit

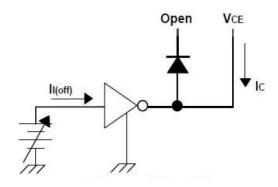


Fig 5. hfe, VCE (sat) Test Circuit

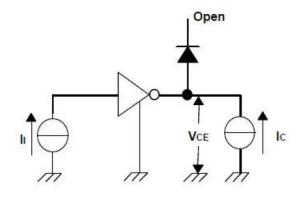


Fig 2. ICEX Test Circuit

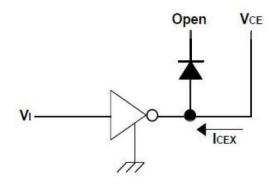


Fig 4. I₁Test Circuit

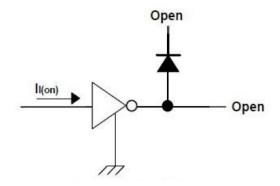


Fig 6. V_{I (on)} Test Circuit

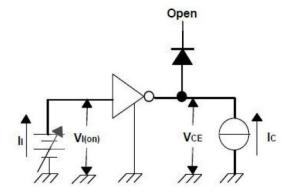




Fig 7. I_R Test Circuit

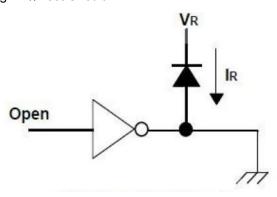


Fig 8. V_F Test Circuit

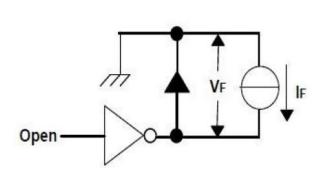
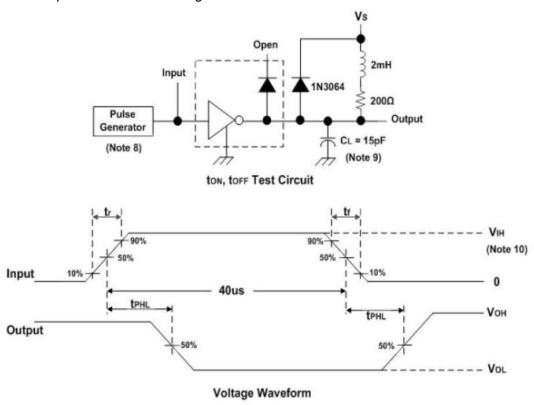


Fig 9. Latch-Up Test Circuit and Voltage Waveform

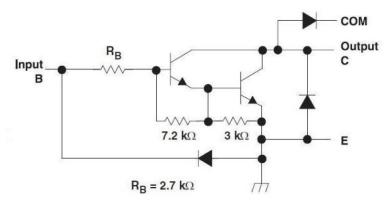


Note

- a. The pulse generator has the following characteristics: Pulse Width=12.5Hz, output impedance 50Ω , tr ≤ 5 ns, tr ≤ 10 ns.
- b. C_L includes prove and jig capacitance.
- c. V_{IH}=3V.

DARLINGTON TRANSISTOR HIGH-CURRENT DARLINGTON TRANSISTOR ARRAYS

BLOCK DIAGRAM



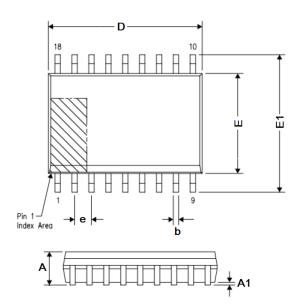
Note:

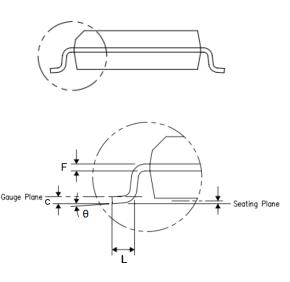
All resistor values shown are nominal.

The collector-emitter diode is a parasitic structure and should not be used to conduct current. If the collector(s) go below ground an external Schottky diode should be added to clamp negative undershoots.

PACKAGE INFORMATION

Dimension in SOP18 Package (Unit: mm)





Symbol	MILLIMETERS			
Symbol	Min.	Max.		
Α	-	2.650		
A1	0.100	0.300		
b	0.310	0.510		
С	0.100	0.250		
D	11.350	11.750		
E	7.400	7.600		
E1	9.970	10.630		
е	1.270 BSC			
F	0.200	0.330		
L	0.400	1.270		
θ	0° 8°			

DARLINGTON TRANSISTOR HIGH-CURRENT DARLINGTON TRANSISTOR ARRAYS

IMPORTANT NOTICE

AiT Semiconductor Inc. (AiT) reserves the right to make changes to any its product, specifications, to discontinue any integrated circuit product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

AiT Semiconductor Inc. integrated circuit products are not designed, intended, authorized, or warranted to be suitable for use in life support applications, devices or systems or other critical applications. Use of AiT products in such applications is understood to be fully at the risk of the customer. As used herein may involve potential risks of death, personal injury, or server property, or environmental damage. In order to minimize risks associated with the customer's applications, the customer should provide adequate design and operating safeguards.

AiT Semiconductor Inc. assumes to no liability to customer product design or application support. AiT warrants the performance of its products of the specifications applicable at the time of sale.